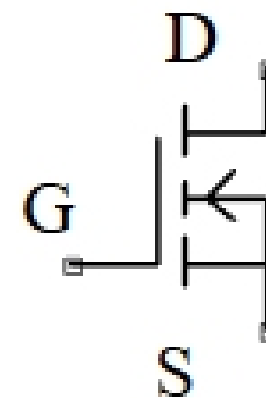
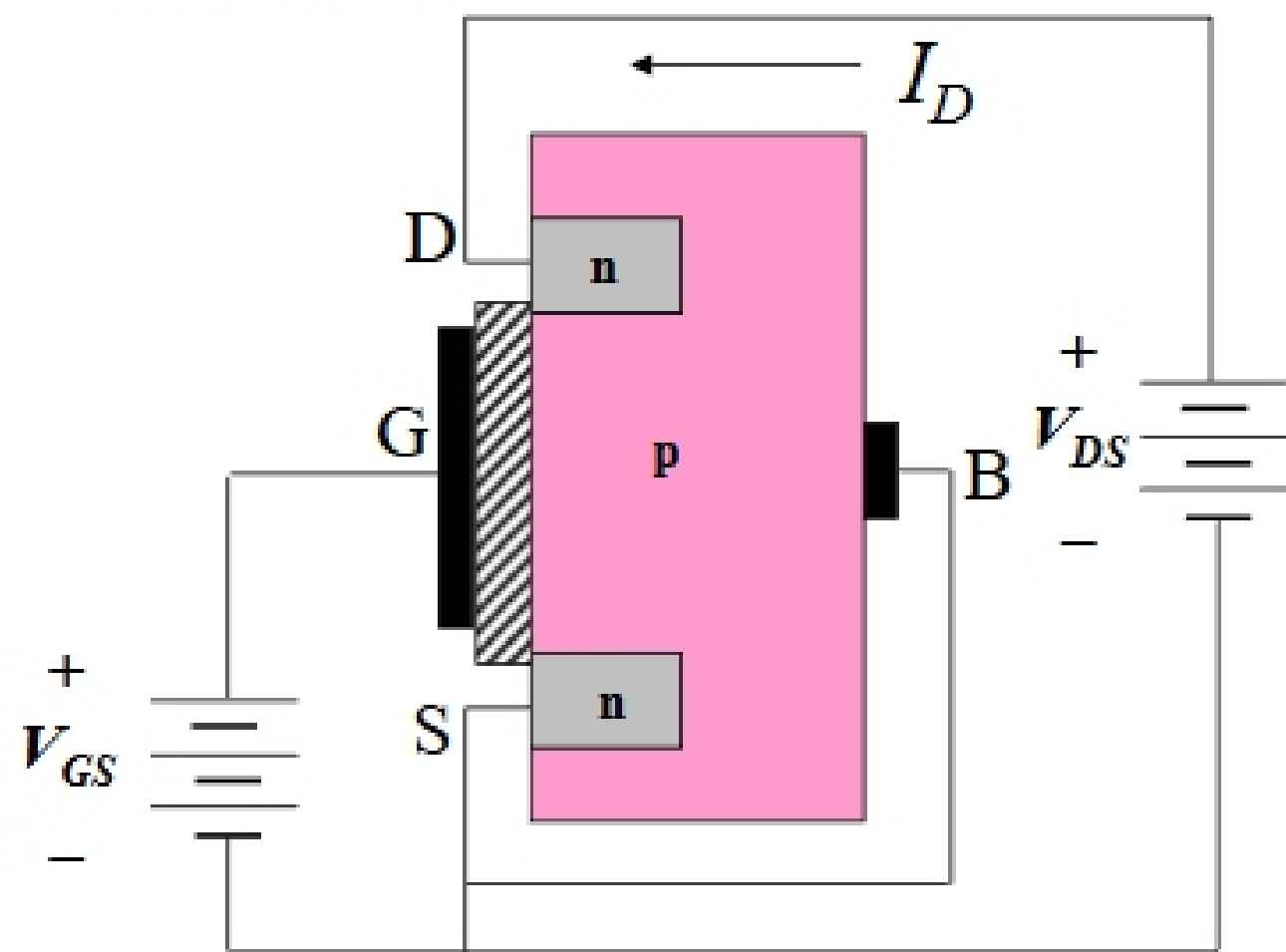


Electronic Circuits Laboratory  
EE462G  
Lab #6

**Biasing MOSFET devices**

# n-Channel MOSFET

**A Metal-Oxide-Semiconductor field-effect transistor (MOSFET) is presented for charge flowing in an n-channel:**



B – Body or Substrate

D – Drain

G – Gate

S – Source

For many applications the body is connected to the source and thus most FETs are packaged that way.

# FET Operation

**The current flow between the drain and the source can be controlled by applying a positive gate voltage:**

